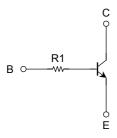
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

# **RN1544**

For use in Muting and Switching Applications.

- Emitter-base voltage is high:  $V_{EBO} = 25 \text{ V (max)}$
- Incorporating a bias resistor into a transistor reduces parts count.
   Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.

#### **Equivalent Circuit**



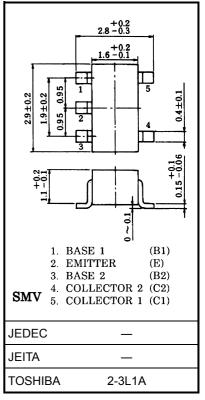
h <sub>FE</sub> classification	А	В
Marking	44A	44B

### Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

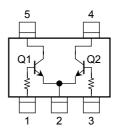
Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	50	V
Collector-emitter voltage	$V_{CEO}$	20	V
Emitter-base voltage	V <sub>EBO</sub>	25	V
Collector current	Ic	300	mA
Collector power dissipation	P <sub>C</sub> (Note1)	300	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	<b>−55~150</b>	°C

Note1: Total rating

Unit: mm



Weight: g (typ.)



Equivalent Circuit (top view)

## Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, I_{E} = 0$	_	_	100	nA
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 25 \text{ V}, I_{C} = 0$	_		100	nA
DC current gain	h <sub>FE</sub> (Note2)	$V_{CE} = 2 \text{ V}, I_C = 4 \text{ mA}$	200		1200	
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1 mA	_	_	0.1	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 6 \text{ V}, I_{C} = 4 \text{ mA}$	_	30	_	MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	_	7	pF
Input resistor	R1	_	1.54	2.2	2.86	kΩ

Note2: hFE classification A: 200~700, B: 350~1200

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